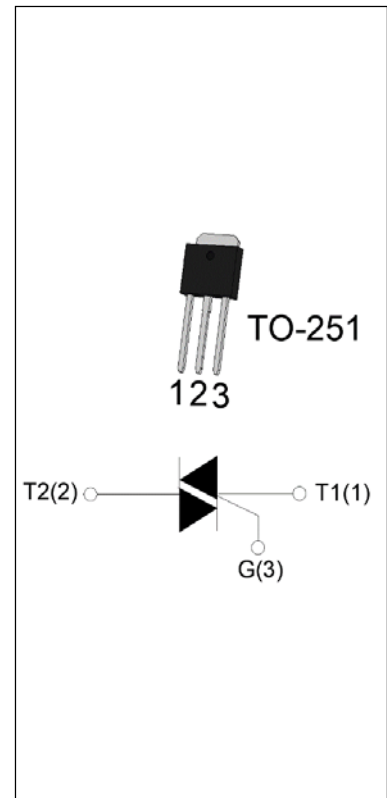


JST02H-1000SW 2A TRIAC

Rev.A.1.0

DESCRIPTION:

The JST02H-1000SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST02H-1000SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM}/V_{RRM}	1000	V
$I_{GT\ I/II/III}$	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1000	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1000	V
RMS on-state current ($T_c \leq 107^\circ\text{C}$)	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	25	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		27.5	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	3.7	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^{\circ}C$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX.	10	mA
V_{GT}		I - II -III	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}C$ $R_L=3.3K\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	20	mA
		II		30	
I_H	$I_T=100mA$		MAX.	15	mA
dV/dt	$V_D=670V$ Gate Open $T_j=125^{\circ}C$		MIN.	300	V/ μs
(dI/dt) _c	(dV/dt) _c =10V/ μs $T_j=125^{\circ}C$		MIN.	1.5	A/ms
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25^{\circ}C$		TYP.	2.5	μs
t_{off}				25	

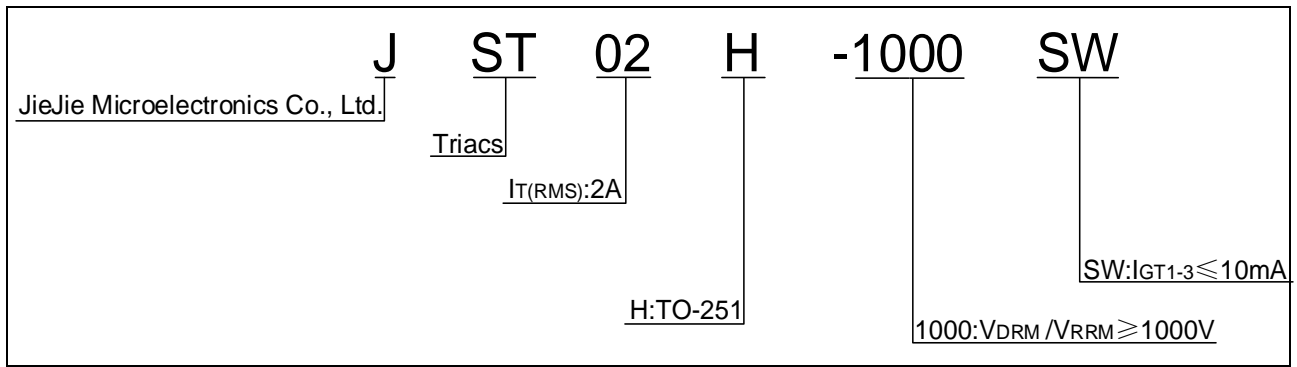
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=3A t_p=380\mu s$	$T_j=25^{\circ}C$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}C$	0.93	V
R_D	Dynamic resistance	$T_j=125^{\circ}C$	146	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}C$	8	μA
I_{RRM}		$T_j=125^{\circ}C$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	6.5	$^{\circ}C/W$
$R_{th(j-a)}$	junction to ambient (AC)	145	$^{\circ}C/W$

ORDERING INFORMATION



MARKING

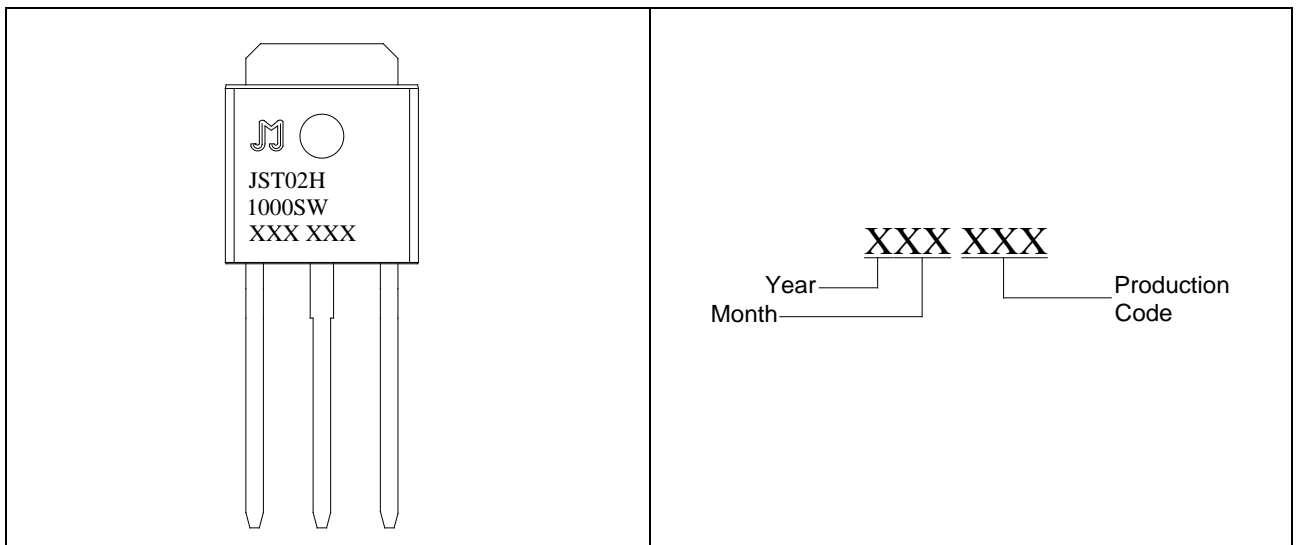


FIG.1 Maximum power dissipation versus RMS on-state current

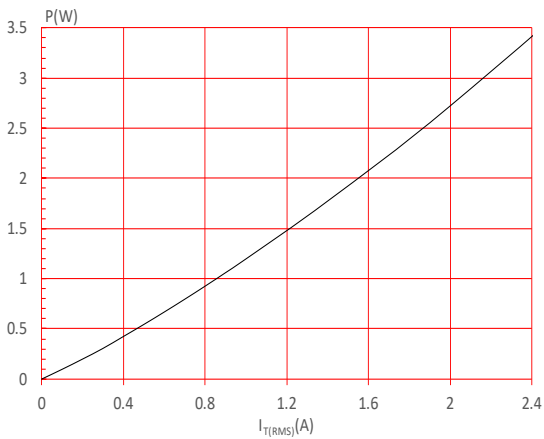


FIG.2: RMS on-state current versus case temperature

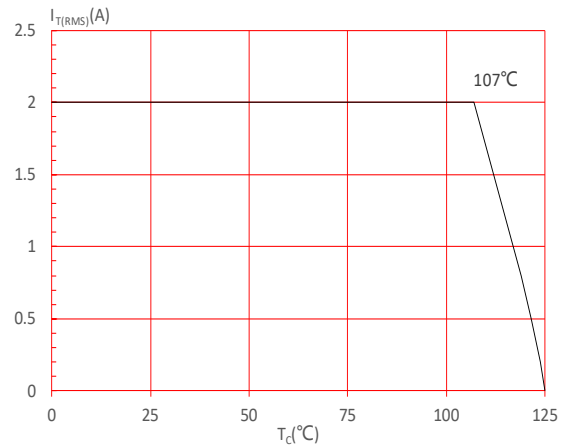


FIG.3: Surge peak on-state current versus number of cycles

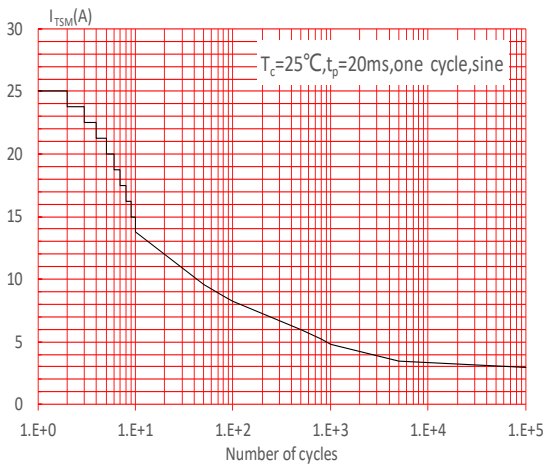


FIG.4: On-state characteristics

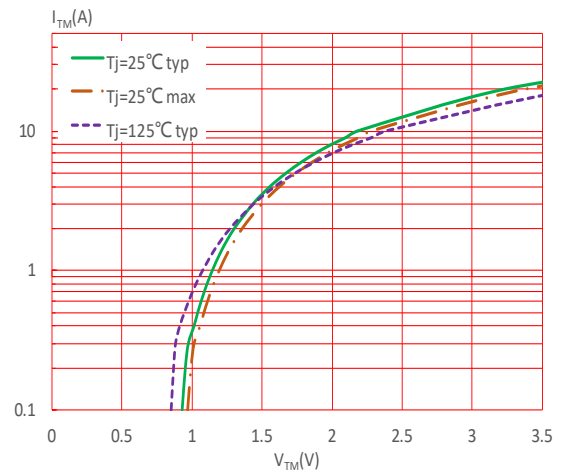


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

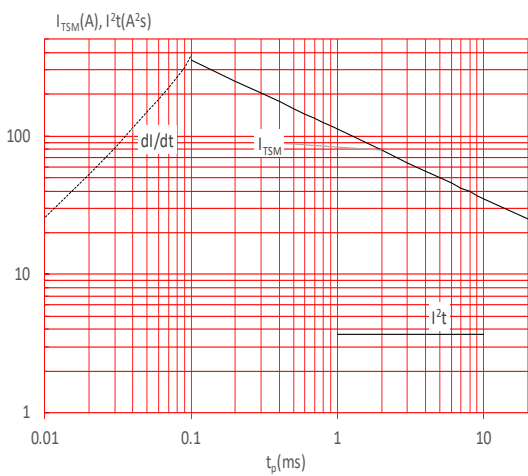


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

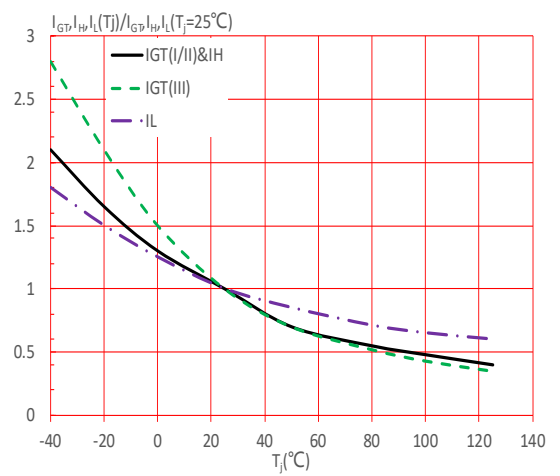
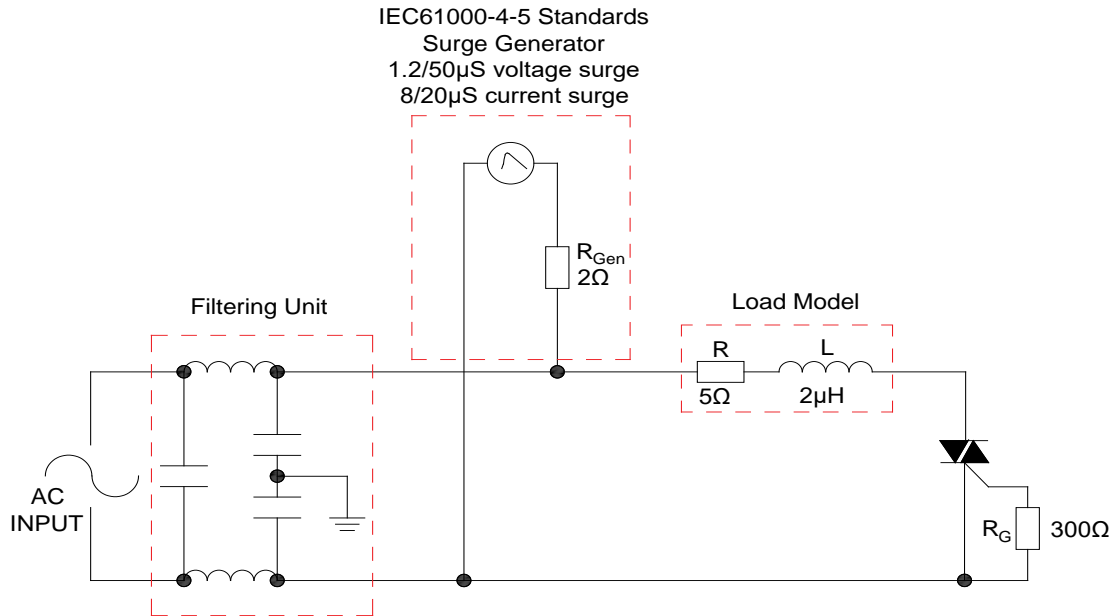


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

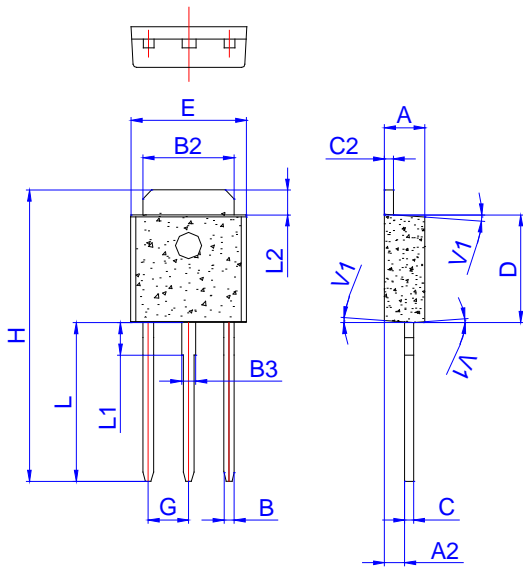
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST02H-1000SW	1000	10	TO-251	80	Tube

Document Revision History

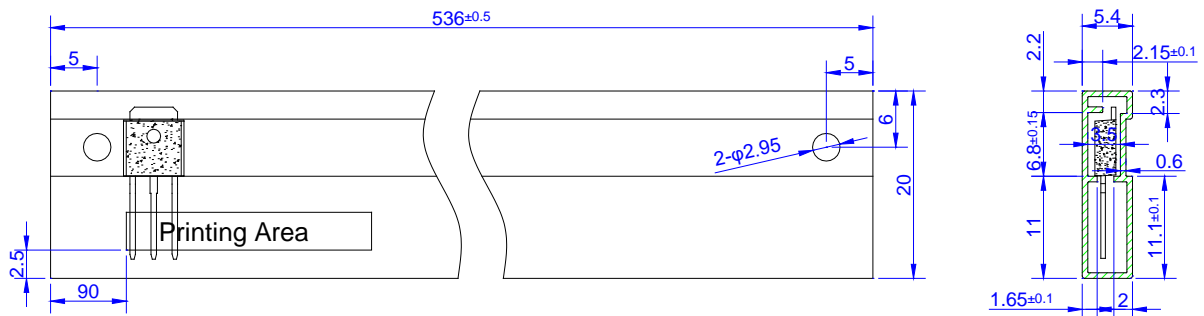
Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1		4°			4°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000

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